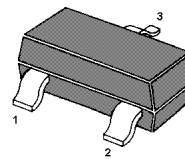


MMBT5400

PNP Silicon Epitaxial Planar Transistor

for high voltage .



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	130	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	120	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current Continuous	$-I_{\text{C}}$	600	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_{\text{amb}}=25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{\text{CE}} = 5\text{ V}$, $-I_{\text{C}} = 10\text{ mA}$	h_{FE}	40	180	-
Collector Base Cutoff Current at $-V_{\text{CB}} = 100\text{ V}$	$-I_{\text{CBO}}$	-	50	nA
Emitter Base Cutoff Current at $-V_{\text{EB}} = 3\text{ V}$	$-I_{\text{EBO}}$	-	50	nA
Collector Base Breakdown Voltage at $-I_{\text{C}} = 0.1\text{ mA}$	$-V_{(\text{BR})\text{CBO}}$	130	-	V
Collector Emitter Breakdown Voltage at $-I_{\text{C}} = 1\text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	120	-	V
Emitter Base Breakdown Voltage at $-I_{\text{E}} = 0.1\text{ mA}$	$-V_{(\text{BR})\text{EBO}}$	5	-	V
Collector Emitter Saturation Voltage at $-I_{\text{C}} = 50\text{ mA}$, $-I_{\text{B}} = 5\text{ mA}$	$-V_{\text{CE}(\text{sat})}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_{\text{C}} = 50\text{ mA}$, $-I_{\text{B}} = 5\text{ mA}$	$-V_{\text{BE}(\text{sat})}$	-	1	V
Current Gain Bandwidth Product at $-V_{\text{CE}} = 10\text{ V}$, $-I_{\text{C}} = 10\text{ mA}$	f_{T}	100	-	MHz
Output Capacitance at $-V_{\text{CB}} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6	pF

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121505007
 ISO 9001 : 2008 Certificate No. 50114012
 OHSAS 18001 : 2007 Certificate No. 0613150806
 IECQ CC 080000 Certificate No. E241M00P HUN2

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